



STP11NM60A

STP11NM60AFP - STB11NM60A-1

N-CHANNEL 600V - 0.4Ω - 11A TO-220/TO-220FP/I²PAK

MDmesh™ Power MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D
STP11NM60A	600 V	<0.45Ω	11 A
STP11NM60AFP	600 V	<0.45Ω	11 A
STB11NM60A-1	600 V	<0.45Ω	11 A

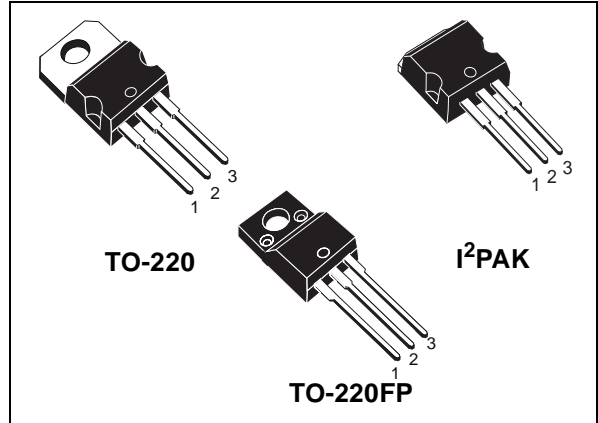
- TYPICAL R_{DS(on)} = 0.4Ω
- HIGH dv/dt
- LOW INPUT CAPACITANCE AND GATE CHARGE
- LOW GATE INPUT RESISTANCE

DESCRIPTION

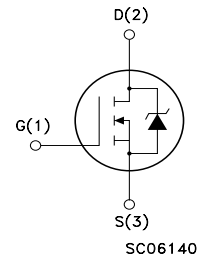
The MDmesh™ is a new revolutionary MOSFET technology that associates the Multiple Drain process with the Company's PowerMESH™ horizontal layout. The resulting product has an outstanding low on-resistance, impressively high dv/dt. The adoption of the Company's proprietary strip technique yields overall dynamic performance that is significantly better than that of similar competition's products.

APPLICATIONS

The MDmesh™ family is very suitable for increasing power density of high voltage converters allowing system miniaturization and higher efficiencies.



INTERNAL SCHEMATIC DIAGRAM



ORDERING INFORMATION

SALES TYPE	MARKING	PACKAGE	PACKAGING
STP11NM60A	P11NM60A	TO-220	TUBE
STP11NM60AFP	P11NM60AFP	TO-220FP	TUBE
STB11NM60A-1	B11NM60A	I ² PAK	TUBE

STP11NM60A/STP11NM60AFP/STB11NM60A-1

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STP11NM60A STB11NM60A-1	STP11NM60AFP	
V _{DS}	Drain-source Voltage (V _{GS} = 0)	600		V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 kΩ)	600		V
V _{GS}	Gate- source Voltage	± 30		V
I _D	Drain Current (continuous) at T _C = 25°C	11	11 (*)	A
I _D	Drain Current (continuous) at T _C = 100°C	7	7 (*)	A
I _{DM} (•)	Drain Current (pulsed)	44	44 (*)	A
P _{TOT}	Total Dissipation at T _C = 25°C	110	35	W
	Derating Factor	0.88	0.28	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	15		V/ns
V _{ISO}	Insulation Withstand Voltage (DC)	-	2500	V
T _j T _{stg}	Operating Junction Temperature Storage Temperature	-55 to 150 -55 to 150		°C °C

(•) Pulse width limited by safe operating area

(1) I_{SD} ≤ 11A, di/dt ≤ 200A/μs, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{JMAX}.

(*) Limited only by maximum temperature allowed

THERMAL DATA

		TO-220 / I ² PAK	TO-220-FP	
R _{thj-case}	Thermal Resistance Junction-case Max	1.13	3.57	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient Max	62.5		°C/W
T _I	Maximum Lead Temperature For Soldering Purpose	300		°C

ON/OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0	600			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating, T _C = 125 °C			1 10	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 20V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	2	3	4	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10V, I _D = 5.5 A		0.4	0.45	Ω

ELECTRICAL CHARACTERISTICS (TCASE =25°C UNLESS OTHERWISE SPECIFIED)

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward Transconductance	$V_{DS} = 15\text{ V}, I_D = 5.5\text{ A}$		10		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 25\text{ V}, f = 1\text{ MHz}, V_{GS} = 0$		1211 248 21		pF pF pF
$C_{oss\ eq.}$ (3)	Equivalent Output Capacitance	$V_{GS} = 0\text{ V}, V_{DS} = 0\text{ V to } 480\text{ V}$		116		pF
R_G	Gate Input Resistance	$f=1\text{ MHz}$ Gate DC Bias = 0 Test Signal Level = 20mV Open Drain		1.9		Ω

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	$V_{DD} = 300\text{ V}, I_D = 5.5\text{ A}$ $R_G = 4.7\Omega, V_{GS} = 10\text{ V}$ (Resistive Load see, Figure 3)		14 15		ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 480\text{ V}, I_D = 11\text{ A},$ $V_{GS} = 10\text{ V}$		35 9 14	49	nC nC nC

SWITCHING OFF

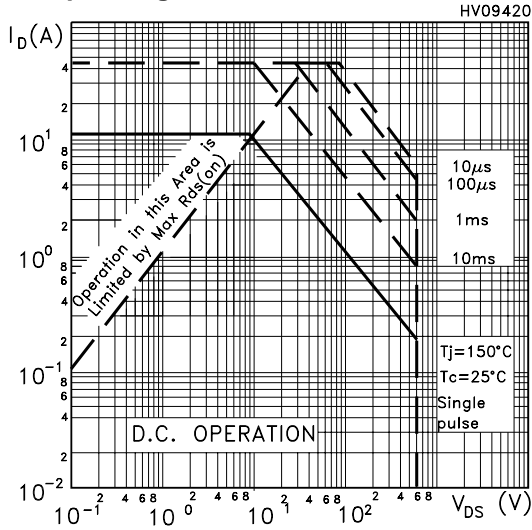
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$ t_f t_c	Off-voltage Rise Time Fall Time Cross-over Time	$V_{DD} = 480\text{ V}, I_D = 11\text{ A},$ $R_G = 4.7\Omega, V_{GS} = 10\text{ V}$ (Inductive Load see, Figure 5)		39 10 20		ns ns ns

SOURCE DRAIN DIODE

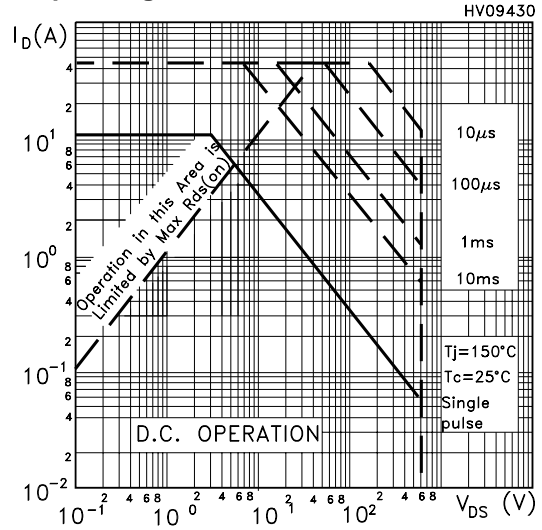
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM} (2)	Source-drain Current Source-drain Current (pulsed)				11 44	A A
V_{SD} (1)	Forward On Voltage	$I_{SD} = 11\text{ A}, V_{GS} = 0$			1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 11\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}, T_j = 150^\circ\text{C}$ (see test circuit, Figure 5)		560 5.7 20.5		ns μC A

- Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.
 2. Pulse width limited by safe operating area.
 3. $C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS} .

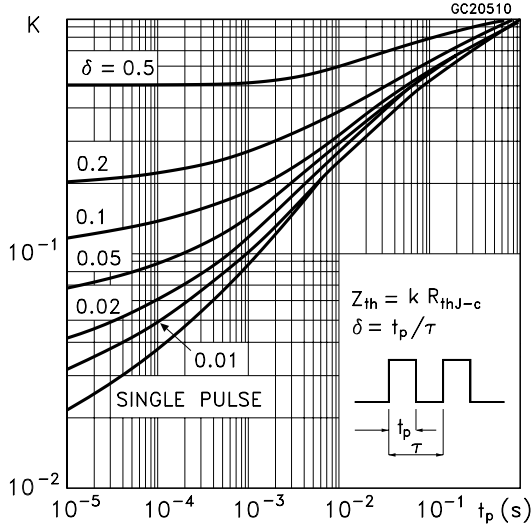
Safe Operating Area for TO-220 / I2PAK



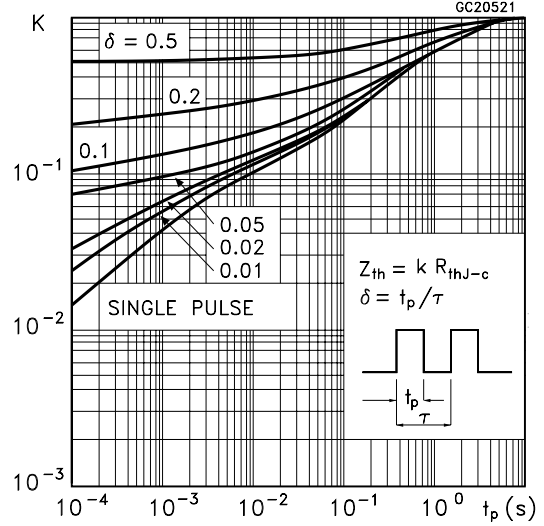
Safe Operating Area for TO-220FP



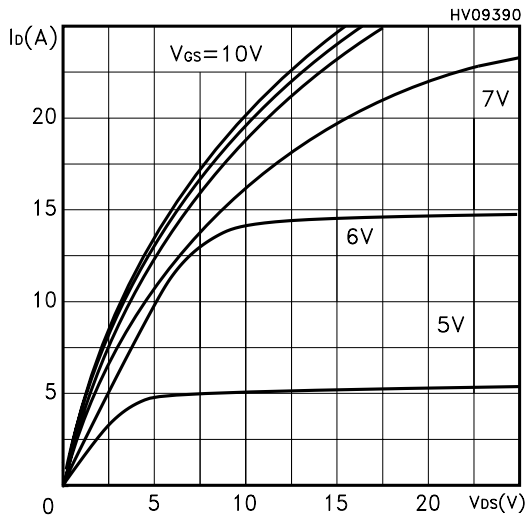
Thermal Impedance for TO-220 / I2PAK



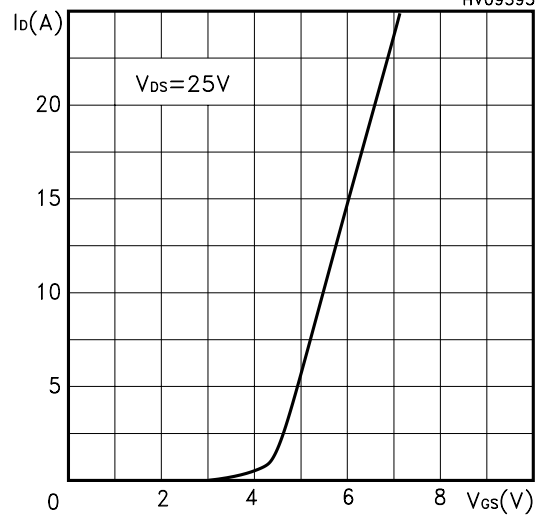
Thermal Impedance for TO-220FP



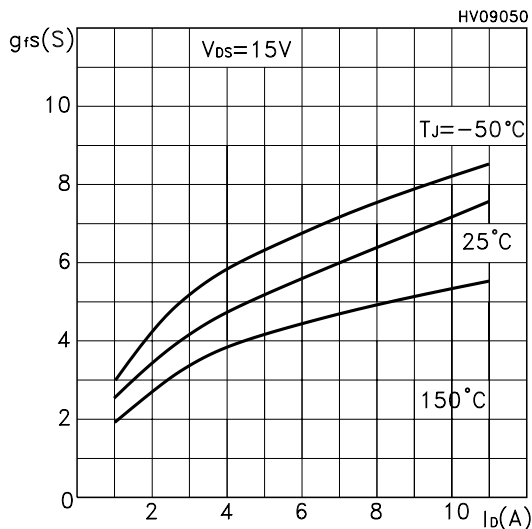
Output Characteristics



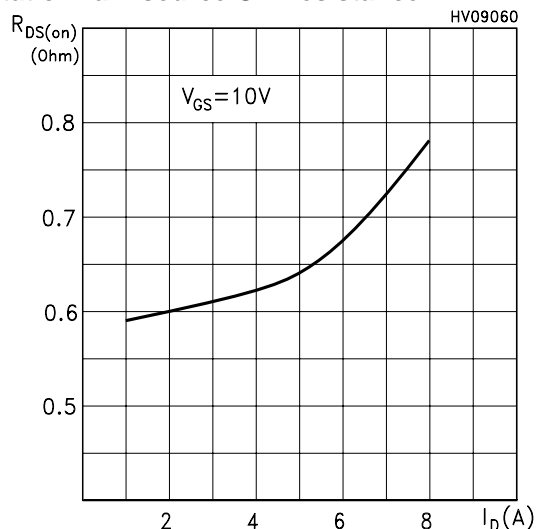
Transfer Characteristics



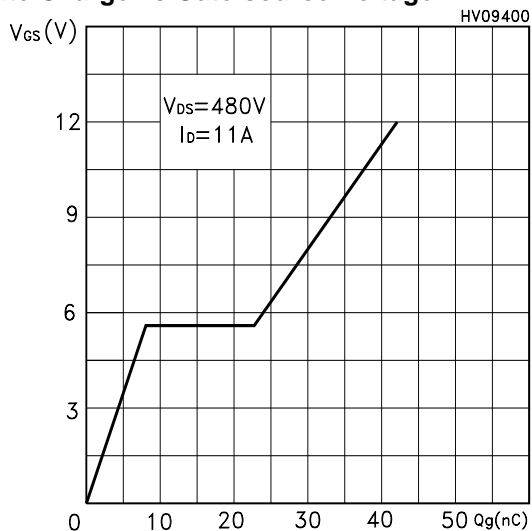
Transconductance



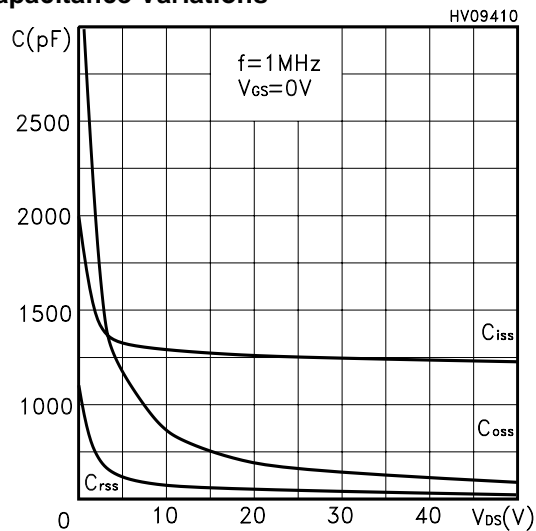
Static Drain-source On Resistance



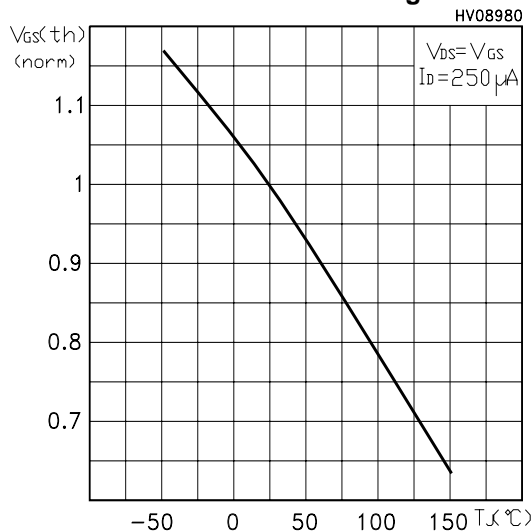
Gate Charge vs Gate-source Voltage



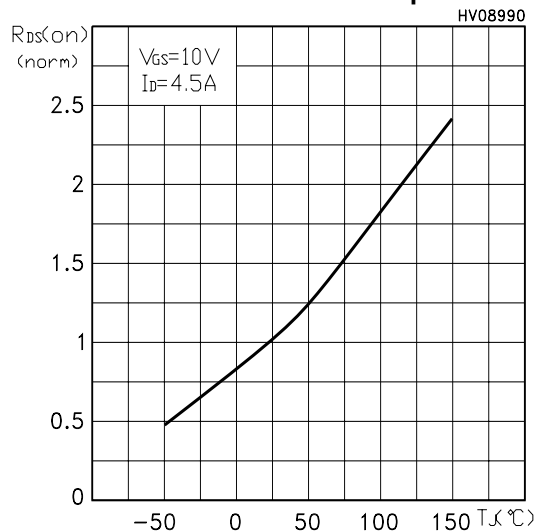
Capacitance Variations



Normalized Gate Threshold Voltage vs Temp.



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

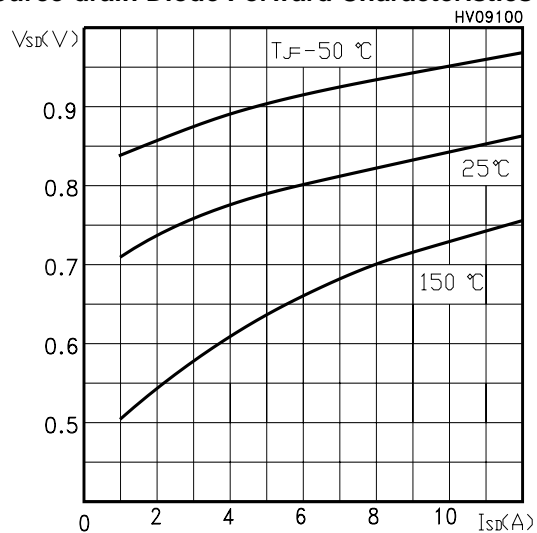


Fig. 1: Unclamped Inductive Load Test Circuit

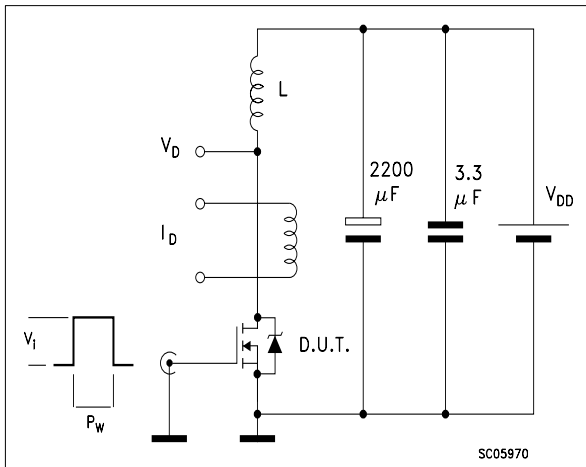


Fig. 2: Unclamped Inductive Waveform

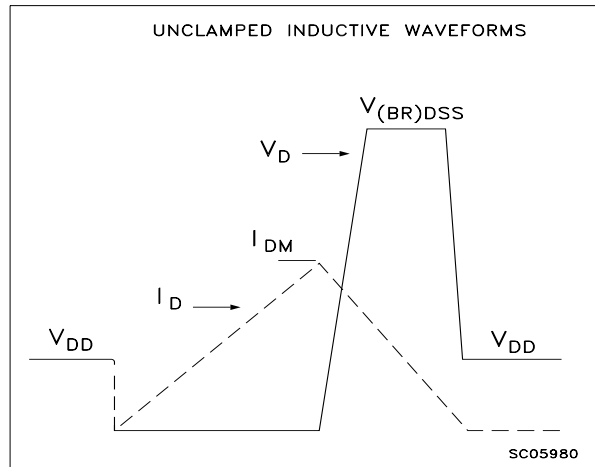


Fig. 3: Switching Times Test Circuit For Resistive Load

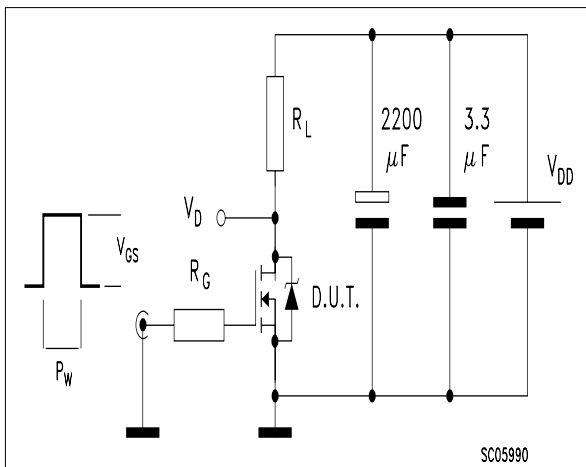


Fig. 4: Gate Charge test Circuit

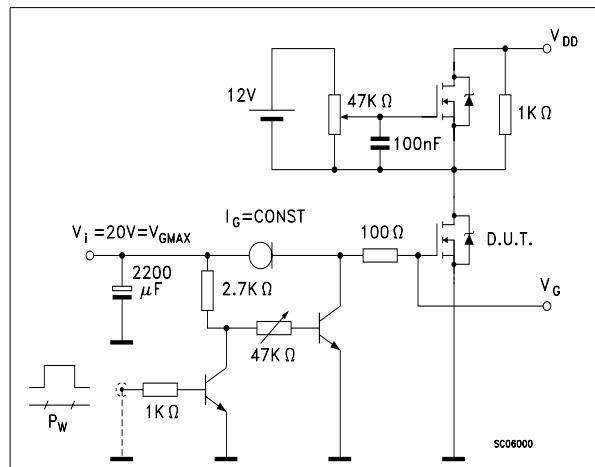
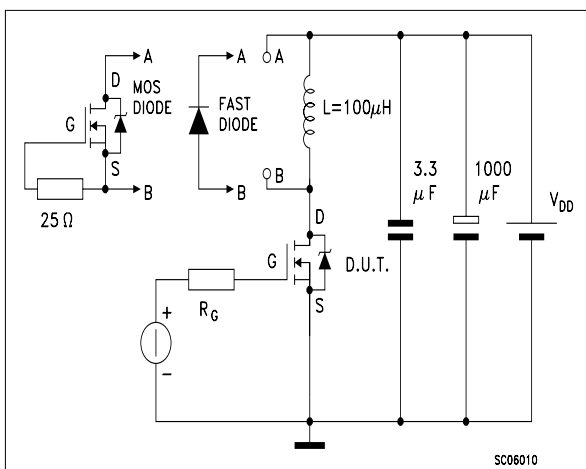
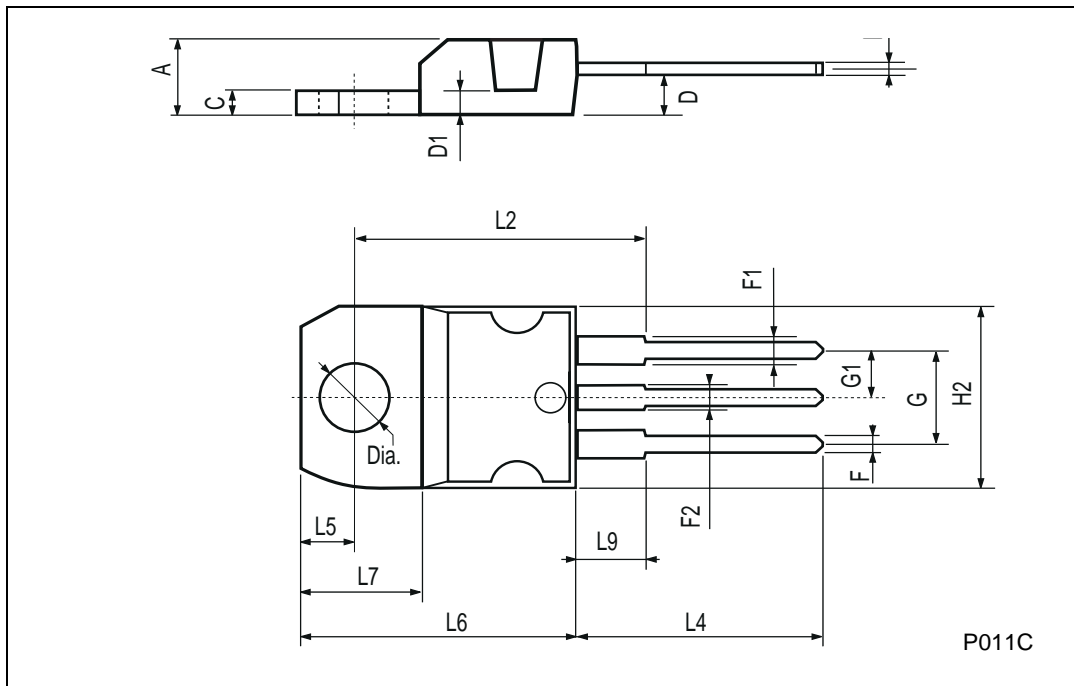


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



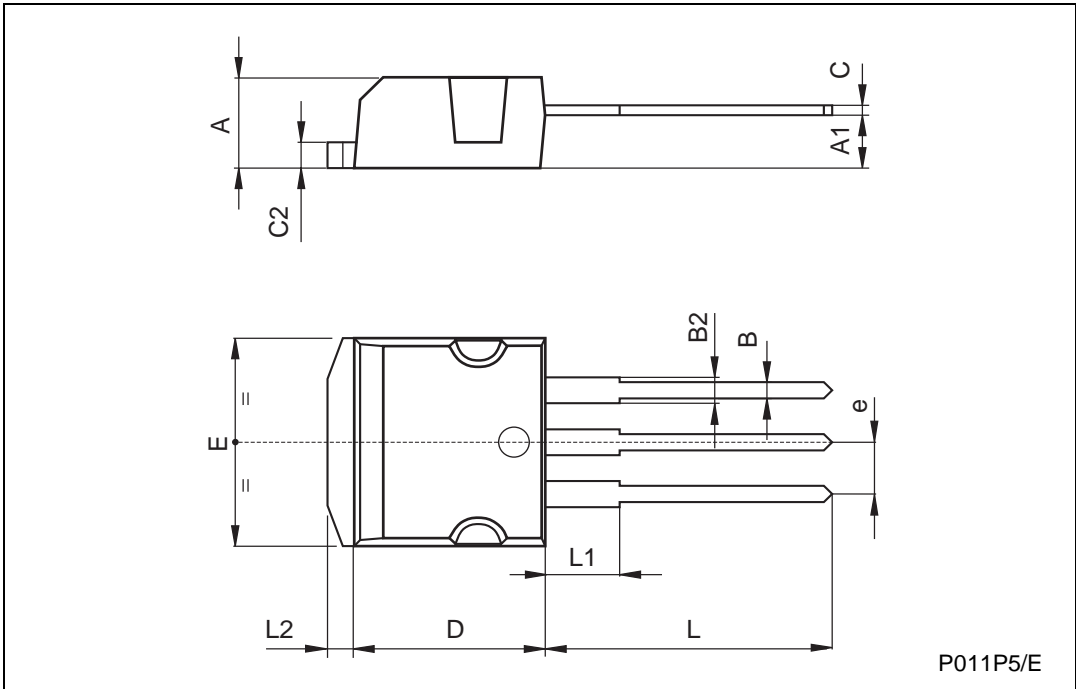
TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



TO-262 (I²PAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
e	2.4		2.7	0.094		0.106
E	10		10.4	0.393		0.409
L	13.1		13.6	0.515		0.531
L1	3.48		3.78	0.137		0.149
L2	1.27		1.4	0.050		0.055



P011P5/E

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